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# R1LV0416D Series

4M SRAM (256-kword  $\times$  16-bit)

REJ03C0311-0100 Rev.1.00 May.24.2007

#### **Description**

The R1LV0416D is a 4-Mbit static RAM organized 256-kword  $\times$  16-bit, fabricated by Renesas's high-performance 0.15 $\mu$ m CMOS and TFT technologies. R1LV0416D Series has realized higher density, higher performance and low power consumption. The R1LV0416D Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. The R1LV0416D Series is packaged in a 44-pin thin small outline mount device, or a 48-ball fine pitch ball grid array.

#### **Features**

Single 3.0 V supply: 2.7 V to 3.6 VFast access time: 55/70 ns (max)

• Power dissipation:

— Standby:  $3 \mu W \text{ (typ) } (V_{CC} = 3.0 \text{ V})$ 

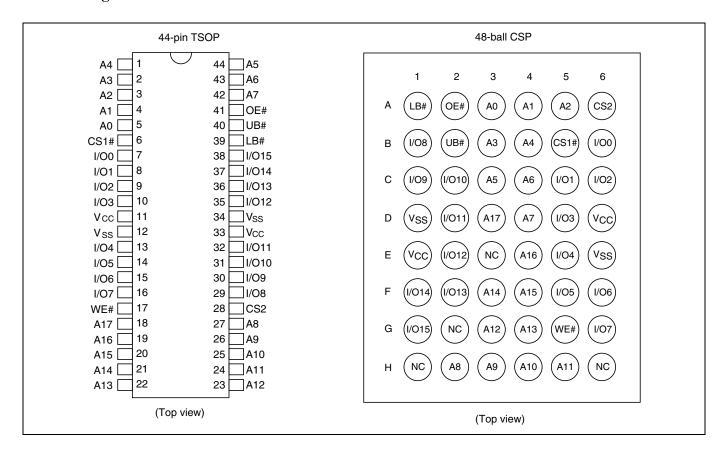
• Equal access and cycle times

- Common data input and output.
  - Three state output
- Battery backup operation.
  - 2 chip selection for battery backup
- Temperature Range: -40 to +85°C

## **Ordering Information**

Type No.	Access time	Package
R1LV0416DSB-5SI	55 ns	400-mil 44-pin plastic TSOP II
R1LV0416DSB-7LI	70 ns	PTSB0044GA-A (44P3W-H)
R1LV0416DBG-5SI	55 ns	48-ball CSP with 0.75 mm ball pitch
R1LV0416DBG-7LI	70 ns	PTBG0048HB-A (48FHH)

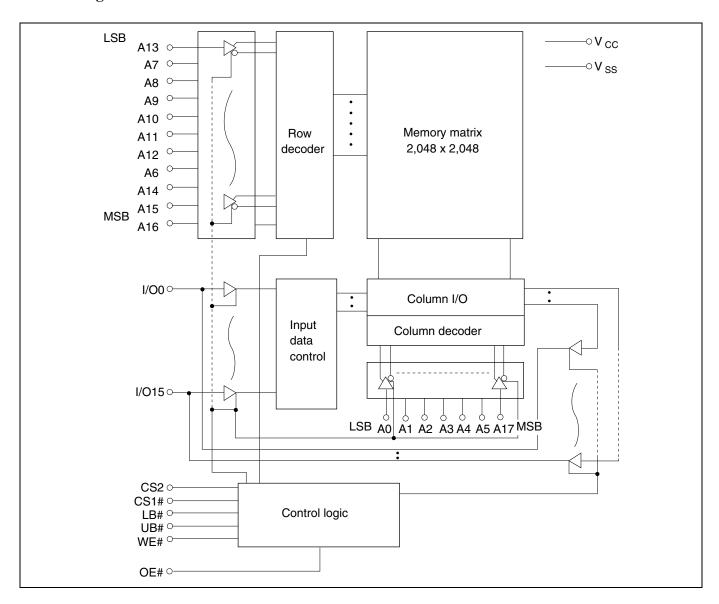
### **Pin Arrangement**



## **Pin Description**

Pin name	Function
A0 to A17	Address input
I/O0 to I/O15	Data input/output
CS1# (CS1)	Chip select 1
CS2	Chip select 2
OE# (OE)	Output enable
WE# (WE)	Write enable
LB# ( <del>LB</del> )	Lower byte select
UB# (UB)	Upper byte select
V <sub>cc</sub>	Power supply
V <sub>ss</sub>	Ground
NC	No connection

## **Block Diagram**



## **Operation Table**

CS1#	CS2	WE#	OE#	UB#	LB#	I/O0 to I/O7	I/O8 to I/O15	Operation
Н	×	×	×	×	×	High-Z	High-Z	Standby
×	L	×	×	×	×	High-Z	High-Z	Standby
×	×	×	×	Н	Н	High-Z	High-Z	Standby
L	Н	Н	L	L	L	Dout	Dout	Read
L	Н	Н	L	Н	L	Dout	High-Z	Lower byte read
L	Н	Н	L	L	Н	High-Z	Dout	Upper byte read
L	Н	L	×	L	L	Din	Din	Write
L	Н	L	×	Н	L	Din	High-Z	Lower byte write
L	Н	L	×	L	Н	High-Z	Din	Upper byte write
L	Н	Н	Н	×	×	High-Z	High-Z	Output disable

Note:  $H: V_{IH}, L: V_{IL}, \times: V_{IH} \text{ or } V_{IL}$ 

## **Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Power supply voltage relative to V <sub>ss</sub>	V <sub>cc</sub>	−0.5 to +4.6	V
Terminal voltage on any pin relative to V <sub>ss</sub>	V <sub>T</sub>	$-0.5^{*1}$ to $V_{cc} + 0.3^{*2}$	V
Power dissipation	P <sub>T</sub>	0.7	W
Operating temperature1	Topr	-40 to +85	°C
Storage temperature range	Tstg	-65 to +150	°C
Storage temperature range under bias	Tbias	-40 to +85	°C

Notes: 1.  $V_{\tau}$  min: -3.0 V for pulse half-width  $\leq 30$  ns.

2. Maximum voltage is +4.6 V.

## **DC Operating Conditions**

Parameter	Symbol	Min	Тур	Max	Unit	Note
Supply voltage	V <sub>cc</sub>	2.7	3.0	3.6	V	
	V <sub>ss</sub>	0	0	0	V	
Input high voltage	V <sub>IH</sub>	2.2	_	V <sub>cc</sub> + 0.3	V	
Input low voltage	V <sub>IL</sub>	-0.3	_	0.6	V	1
Ambient temperature range	Та	-40	_	+85	°C	

Note: 1.  $V_{\parallel}$  min: -3.0 V for pulse half-width  $\leq 30$  ns.

### **DC** Characteristics

Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
Input leakage current			I <sub>LI</sub>	_	_	1	μΑ	Vin = V <sub>ss</sub> to V <sub>cc</sub>
Output leakage current			I <sub>LO</sub>	_		1	μА	$CS1\# = V_{ H}$ or $CS2 = V_{ L}$ or $OE\# = V_{ H}$ or $WE\# = V_{ L}$ or $LB\# = UB\# = V_{ H}$ , $V_{ VO} = V_{ SS}$ to $V_{ CC}$
Operating current			I <sub>cc</sub>			20	mA	$CS1# = V_{IL}, CS2 = V_{IH},$ Others = $V_{IH}/V_{IL}, I_{I/O} = 0 \text{ mA}$
Average operating cu	rrent		I <sub>cc1</sub>		_	25	mA	Min. cycle, duty = 100%, $I_{I/O} = 0$ mA, CS1# = $V_{IL}$ , CS2 = $V_{IH}$ , Others = $V_{IH}/V_{IL}$
			I <sub>CC2</sub>	_		5	mA	Cycle time = 1 $\mu$ s, duty = 100%, $I_{\text{I/O}} = 0$ mA, CS1# $\leq$ 0.2 V, CS2 $\geq$ V <sub>CC</sub> $-$ 0.2 V $V_{\text{IH}} \geq$ V <sub>CC</sub> $-$ 0.2 V, $V_{\text{IL}} \leq$ 0.2 V
Standby current			I <sub>SB</sub>	_	0.1*1	0.3	mA	CS2 = V <sub>IL</sub>
Standby current	-5SI	to +85°C	I <sub>SB1</sub>	_	_	10	μΑ	Vin ≥ 0 V
		to +70°C	I <sub>SB1</sub>	_	_	8	μΑ	(1) 0 V ≤ CS2 ≤ 0.2 V or
		to +40°C	I <sub>SB1</sub>	_	_	3	μΑ	(2) CS1# $\geq$ V <sub>cc</sub> $-$ 0.2 V,
		to +25°C	I <sub>SB1</sub>	_	<b>1</b> * <sup>1</sup>	2.5	μΑ	$CS2 \ge V_{cc} - 0.2 \text{ V or}$
	-7LI	to +85°C	I <sub>SB1</sub>	_	_	20	μΑ	(3) LB# = UB# ≥ V <sub>cc</sub> – 0.2 V,
		to +70°C	I <sub>SB1</sub>	_	_	16	μΑ	CS2 ≥ V <sub>cc</sub> – 0.2 V,
	to +40°C		I <sub>SB1</sub>	_	_	10	μΑ	CS1# ≤ 0.2 V
to +25°C			I <sub>SB1</sub>	_	<b>1</b> *1	10	μΑ	Average values
Output high voltage			V <sub>OH</sub>	2.4	_	_	V	$I_{OH} = -1 \text{ mA}$
			V <sub>OH2</sub>	V <sub>cc</sub> - 0.2	_	_	V	$I_{OH} = -100  \mu A$
Output low voltage			V <sub>oL</sub>	_	_	0.4	V	I <sub>oL</sub> = 2 mA
			V <sub>OL2</sub>	_	_	0.2	V	$I_{OL} = 100 \mu A$

Note: 1. Typical values are at  $V_{cc} = 3.0 \text{ V}$ ,  $Ta = +25^{\circ}\text{C}$  and specified loading, and not guaranteed.

## Capacitance

 $(Ta = +25^{\circ}C, f = 1.0 \text{ MHz})$ 

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions	Note
Input capacitance	Cin	_	_	8	pF	Vin = 0 V	1
Input/output capacitance	C <sub>I/O</sub>	_	_	10	pF	V <sub>1/0</sub> = 0 V	1

Note: 1. This parameter is sampled and not 100% tested.

### **AC Characteristics**

 $(Ta = -40 \text{ to } +85^{\circ}\text{C}, \ V_{_{CC}} = 2.7 \ \text{V to } 3.6 \ \text{V})$ 

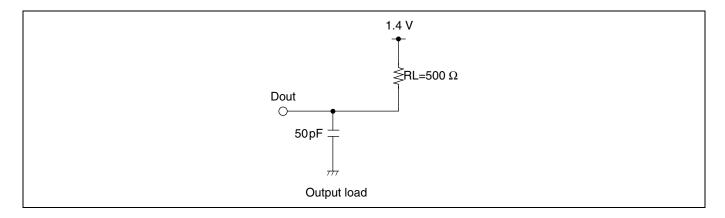
#### **Test Conditions**

Input pulse levels:  $V_{IL} = 0.4 \text{ V}$ ,  $V_{IH} = 2.4 \text{ V}$ 

• Input rise and fall time: 5 ns

• Input/output timing reference levels: 1.4 V

• Output load: See figures (Including scope and jig)



## R1LV0416D Series

## Read Cycle

			R1LV	0416D				
		-5	SI	-7	'LI			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes	
Read cycle time	t <sub>RC</sub>	55	_	70	_	ns		
Address access time	t <sub>AA</sub>	_	55	_	70	ns		
Chip select access time	t <sub>ACS1</sub>	_	55	_	70	ns		
	t <sub>ACS2</sub>	_	55	_	70	ns		
Output enable to output valid	t <sub>oe</sub>	_	35	_	40	ns		
Output hold from address change	t <sub>oh</sub>	10	_	10	_	ns		
LB#, UB# access time	t <sub>BA</sub>	_	55	_	70	ns		
Chip select to output in low-Z	t <sub>CLZ1</sub>	10	_	10	_	ns	2, 3	
	t <sub>CLZ2</sub>	10	_	10	_	ns	2, 3	
LB#, UB# disable to low-Z	t <sub>BLZ</sub>	5	_	5	_	ns	2, 3	
Output enable to output in low-Z	t <sub>oLZ</sub>	5	_	5	_	ns	2, 3	
Chip deselect to output in high-Z	t <sub>cHZ1</sub>	0	20	0	25	ns	1, 2, 3	
	t <sub>CHZ2</sub>	0	20	0	25	ns	1, 2, 3	
LB#, UB# disable to high-Z	t <sub>BHZ</sub>	0	20	0	25	ns	1, 2, 3	
Output disable to output in high-Z	t <sub>ohz</sub>	0	20	0	25	ns	1, 2, 3	

#### Write Cycle

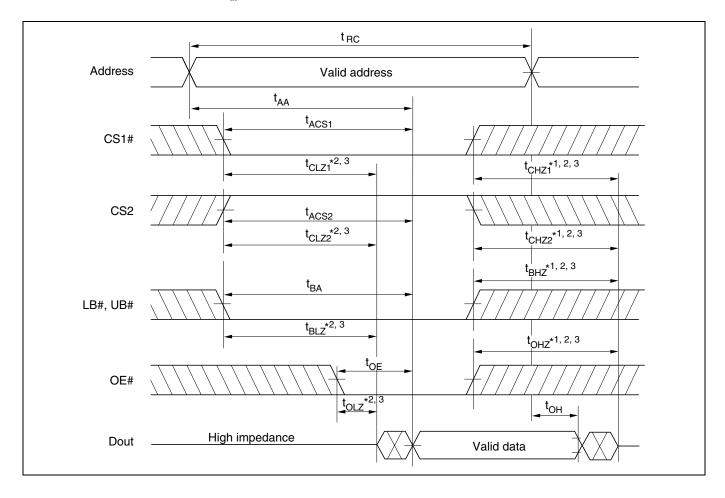
			R1LV				
		-5	SI	-7	'LI		
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write cycle time	t <sub>wc</sub>	55	_	70	_	ns	
Address valid to end of write	t <sub>AW</sub>	50	_	60	_	ns	
Chip selection to end of write	t <sub>cw</sub>	50	_	60	_	ns	5
Write pulse width	t <sub>wP</sub>	40	_	50	_	ns	4
LB#, UB# valid to end of write	t <sub>BW</sub>	50	_	55	_	ns	
Address setup time	t <sub>AS</sub>	0	_	0	_	ns	6
Write recovery time	t <sub>wR</sub>	0	_	0	_	ns	7
Data to write time overlap	t <sub>DW</sub>	25	_	30	_	ns	
Data hold from write time	t <sub>DH</sub>	0	_	0	_	ns	
Output active from end of write	t <sub>ow</sub>	5	_	5	_	ns	2
Output disable to output in high-Z	t <sub>oHZ</sub>	0	20	0	25	ns	1, 2, 3
Write to output in high-Z	t <sub>wHZ</sub>	0	20	0	25	ns	1, 2

Notes: 1.  $t_{\text{CHZ}}, t_{\text{OHZ}}, t_{\text{WHZ}}$  and  $t_{\text{BHZ}}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

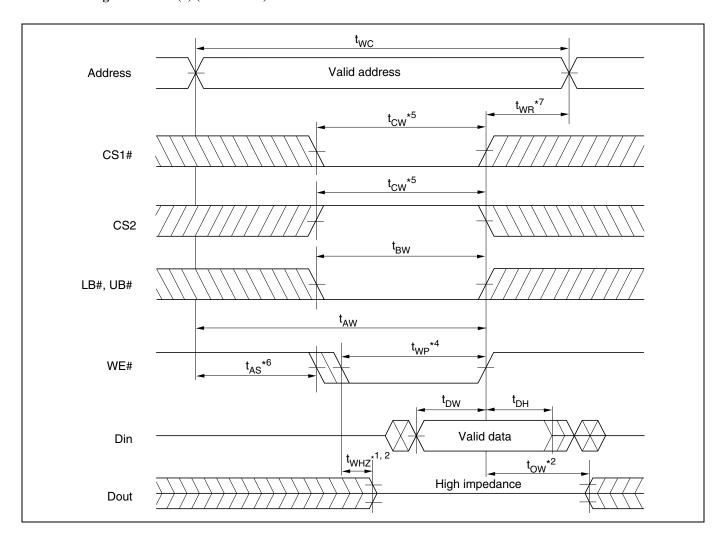
- 2. This parameter is sampled and not 100% tested.
- 3. At any given temperature and voltage condition,  $t_{HZ}$  max is less than  $t_{LZ}$  min both for a given device and from device to device.
- 4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#. A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low. A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. t<sub>wp</sub> is measured from the beginning of write to the end of write.
- 5.  $t_{cw}$  is measured from the later of CS1# going low or CS2 going high to the end of write.
- 6.  $t_{AS}$  is measured from the address valid to the beginning of write.
- 7. t<sub>ws</sub> is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.

## **Timing Waveform**

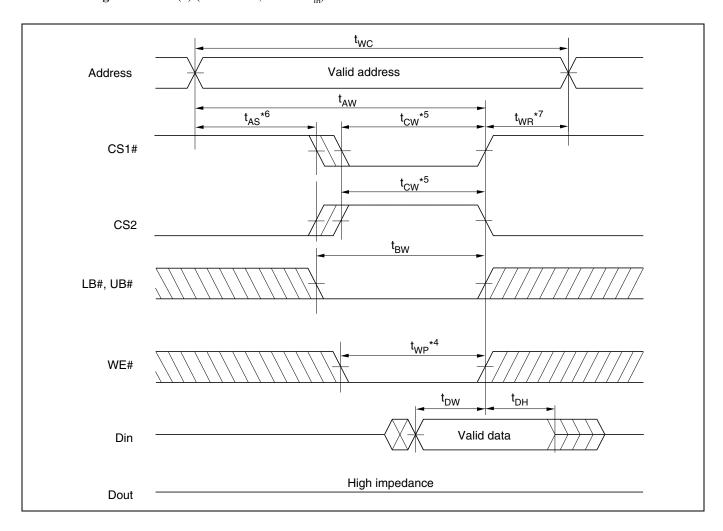
**Read Timing Waveform** (WE# =  $V_{IH}$ )



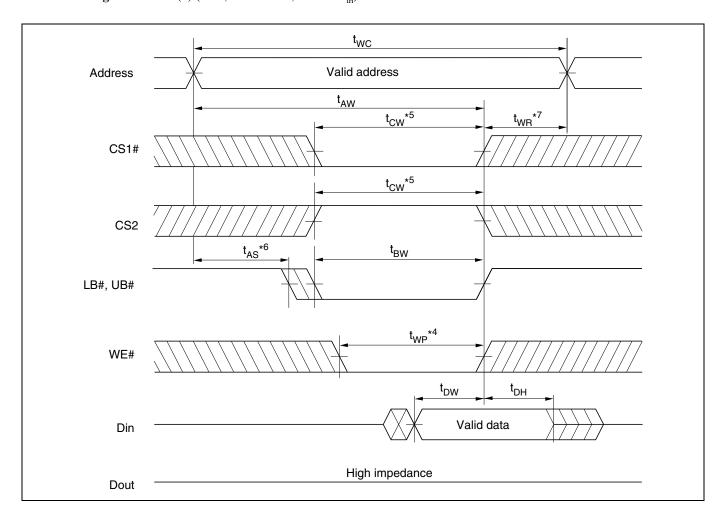
## Write Timing Waveform (1) (WE# Clock)



## Write Timing Waveform (2) (CS# Clock, OE# = $V_{H}$ )



Write Timing Waveform (3) (LB#, UB# Clock, OE# =  $V_{H}$ )



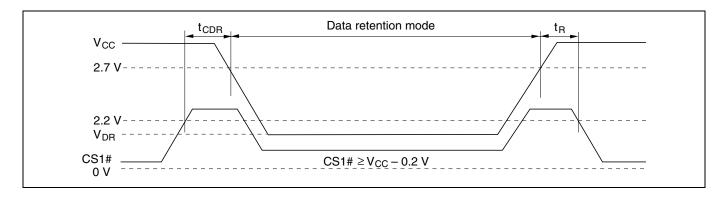
# Low $\boldsymbol{V}_{\!\scriptscriptstyle CC}$ Data Retention Characteristics

 $(Ta = -40 \text{ to } +85^{\circ}C)$ 

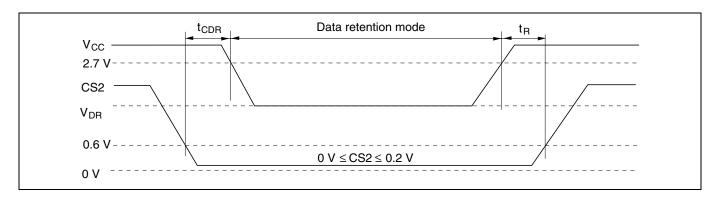
Parameter			Symbol	Min	Тур	Max	Unit	Test conditions
$V_{\infty}$ for data r	V <sub>DR</sub>	2.0	_	_	V	$\begin{aligned} &\text{Vin} \ge 0\text{V} \\ &(1) \ 0 \ \text{V} \le \text{CS2} \le 0.2 \ \text{V} \ \text{or} \\ &(2) \ \text{CS2} \ge \text{V}_{\text{CC}} - 0.2 \ \text{V}, \\ &\text{CS1\#} \ge \text{V}_{\text{CC}} - 0.2 \ \text{V} \ \text{or} \\ &(3) \ \text{LB\#} = \text{UB\#} \ge \text{V}_{\text{CC}} - 0.2 \ \text{V}, \\ &\text{CS2} \ge \text{V}_{\text{CC}} - 0.2 \ \text{V}, \\ &\text{CS1\#} \le 0.2 \ \text{V} \end{aligned}$		
Data	-5SI	to +85°C	I <sub>CCDR</sub>	_		10	μA	V <sub>cc</sub> = 3.0 V, Vin ≥ 0V
retention current		to +70°C	I <sub>CCDR</sub>	_		8	μΑ	(1) $0 \text{ V} \le \text{CS2} \le 0.2 \text{ V} \text{ or}$ (2) $\text{CS2} \ge \text{V}_{cc} - 0.2 \text{ V},$
Carroni		to +40°C	I <sub>CCDR</sub>	_	_	3	μΑ	$CS1\# \ge V_{cc} - 0.2 \text{ V or}$
		to +25°C	I <sub>CCDR</sub>	_	<b>1</b> *1	2.5	μΑ	(3) LB# = UB# $\geq$ V <sub>cc</sub> $- 0.2$ V,
	-7LI	to +85°C	I <sub>CCDR</sub>	_		20	μΑ	$CS2 \ge V_{CC} - 0.2 \text{ V},$ $CS1\# \le 0.2 \text{ V}$
		to +70°C	I <sub>CCDR</sub>	_	_	16	μΑ	Average values
		to +40°C	I <sub>CCDR</sub>	_	_	10	μΑ	
	CCDR	_	1*1	10	μΑ			
Chip deselect to data retention time			t <sub>cdr</sub>	0		_	ns	See retention waveform
Operation red	covery time		t <sub>R</sub>	5		_	ms	

Note: 1. Typical values are at  $V_{cc} = 3.0 \text{ V}$ ,  $Ta = +25^{\circ}\text{C}$  and specified loading, and not guaranteed.

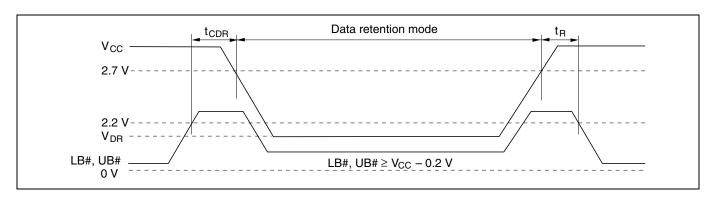
Low  $V_{\rm cc}$  Data Retention Timing Waveform (1) (CS1# Controlled)



Low  $V_{cc}$  Data Retention Timing Waveform (2) (CS2 Controlled)



Low  $V_{\rm cc}$  Data Retention Timing Waveform (3) (LB#, UB# Controlled)



## **Revision History**

## **R1LV0416D Series Data Sheet**

Rev.	Date		Contents of Modification
		Page	Description
0.01	Dec. 25, 2006	_	Initial issue
1.00	May. 24, 2007	2	Ordering Information
			R1LV0416DSB-5S% to R1LV0416DSB-5SI
			R1LV0416DSB-7L% to R1LV0416DSB-7LI
			R1LV0416DBG-5S% to R1LV0416DBG-5SI
			R1LV0416DBG-7L% to R1LV0416DBG-7LI
		3	Pin Arrangement
			A6 to A13, A13 to A6
		4	Change of Block Diagram
		5	Absolute Maximum Ratings: Deletion of R ver. specification
		5	DC Operating Conditions: Deletion of R ver. specification
		6	DC Characteristics
			I <sub>SB1</sub> (-5SI) (to +25°C) max: 3 μA to 2.5 μA
		7	AC Characteristics: Change of Test Conditions
		14	Low V <sub>CC</sub> Data Retention Characteristics
			I <sub>CCDR</sub> (-5SI) (to +25°C) max: 3 μA to 2.5 μA
			Deletion of note 2

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